AMENDMENTS TO THE CLAIMS:

Please amend the Claims as follows:

1 – 5. (Cancelled)

6. (Currently Amended) A manufacturing process for a silicon epitaxial wafer comprising the steps of:

forming an epitaxial layer on a silicon substrate with an interstitial oxygen concentration in a range of from 4 x $10^{17}/cm^3$ to 10 x $10^{17}/cm^3$ at a temperature of 1000° C or higher to obtain a silicon epitaxial wafer; and

applying heat treatment to the silicon epitaxial wafer at a temperature in a range of from 450° C to 750° C;

thereby forming new oxygen precipitation nuclei and increasing bulk defect density, without reducing internal gettering;

wherein a substrate resistivity of the epitaxial wafer is 0.02 Ω-cm or lower.

7. (Previously Presented) The manufacturing process for a silicon epitaxial wafer according to claim 6, wherein the interstitial oxygen concentration is in a range of from 6 x $10^{17}/cm^3$ to 10 x $10^{17}/cm^3$.

8. (Previously Presented) The manufacturing process for a silicon epitaxial wafer according to claim 6, wherein the heat treatment temperature is in a range of from 500° C to 700° C.

9. (Previously Presented) The manufacturing process for a silicon epitaxial wafer according to claim 7, wherein the heat treatment temperature is in a range of from 500° C to 700° C.

10. Cancel

11. Cancel

12. Cancel

13. Cancel

14. (Previously Presented) The manufacturing process for a silicon epitaxial wafer according to claim 6, wherein a dopant in a substrate of the silicon epitaxial wafer is boron, arsenic or antimony.

15. (Previously Presented) The manufacturing process for a silicon epitaxial wafer according to claim 7, wherein a dopant in a substrate of the silicon epitaxial wafer is boron, arsenic or antimony.

16. (Previously Presented) The manufacturing process for a silicon epitaxial wafer according to claim 8, wherein a dopant in a substrate of the silicon epitaxial wafer is boron, arsenic or antimony.

17. (Previously Presented) The manufacturing process for a silicon epitaxial wafer according to claim 9, wherein a dopant in a substrate of the silicon epitaxial wafer is boron, arsenic or antimony.

18. Cancel

19. Cancel

20. Cancel

21. Cancel